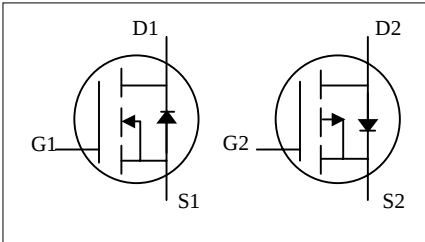
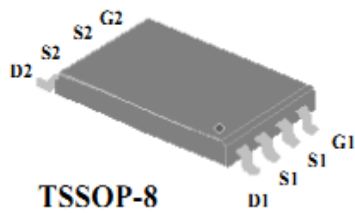


N- and P-Channel 30-V (D-S) MOSFET

- ▼ Simple Drive Requirement
- ▼ Lower Gate Charge
- ▼ Fast Switching Performance
- ▼ RoHS Compliant & Halogen-Free

N-CH	BV_{DSS}	30V
	$R_{DS(ON)}$	22m Ω
	I_D	6.2A
P-CH	BV_{DSS}	-30V
	$R_{DS(ON)}$	45m Ω
	I_D	-5.0A



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_D@T_A=25^{\circ}\text{C}$	Continuous Drain Current ³	6.2	-5.0	A
$I_D@T_A=70^{\circ}\text{C}$	Continuous Drain Current ³	5.0	-4.0	A
I_{DM}	Pulsed Drain Current ¹	20	-18	A
$P_D@T_A=25^{\circ}\text{C}$	Total Power Dissipation	1.35		W
T_{STG}	Storage Temperature Range	-55 to 150		$^{\circ}\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150		$^{\circ}\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	90	$^{\circ}\text{C}/\text{W}$

N-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =6A	-	22	-	mΩ
		V _{GS} =4.5V, I _D =4A	-	30	-	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =6A	-	14	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V	-	-	1	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =6A	-	7	11	nC
Q _{gs}	Gate-Source Charge	V _{DS} =15V	-	2	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	4	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V	-	6	-	ns
t _r	Rise Time	I _D =1A	-	6	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	17	-	ns
t _f	Fall Time	V _{GS} =10V	-	4	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	550	-	pF
C _{oss}	Output Capacitance	V _{DS} =15V	-	105	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	90	-	pF
R _g	Gate Resistance	f=1.0MHz	-	1.7	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =1.2A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	I _S =6A, V _{GS} =0V,	-	15	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	-	7	-	nC

P-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-5A	-	45	-	mΩ
		V _{GS} =-4.5V, I _D =-3A	-	66	-	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-3	V
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-5A	-	18	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V	-	-	-1	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =-5A	-	14.4	23	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V	-	5.5	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	5	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-15V	-	7	-	ns
t _r	Rise Time	I _D =-1A	-	6.5	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	36	-	ns
t _f	Fall Time	V _{GS} =-10V	-	28	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	960	-	pF
C _{oss}	Output Capacitance	V _{DS} =-15V	-	190	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	170	-	pF
R _g	Gate Resistance	f=1.0MHz	-	6	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-1.2A, V _{GS} =0V	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	I _S =-5A, V _{GS} =0V,	-	19	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	9	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in² copper pad of FR4 board , t ≤10sec ; 208°C/W when mounted on min. copper pad.

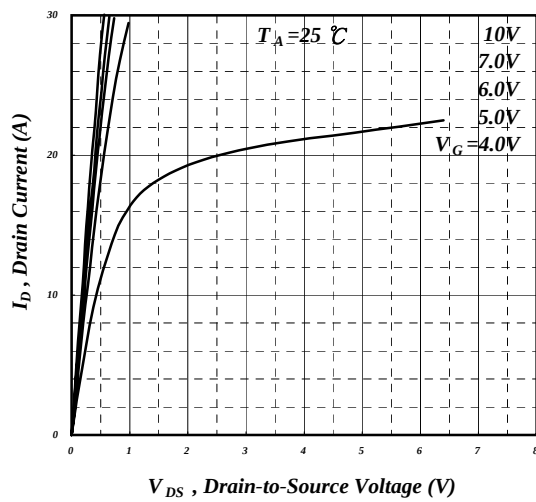


Fig 1. Typical Output Characteristics

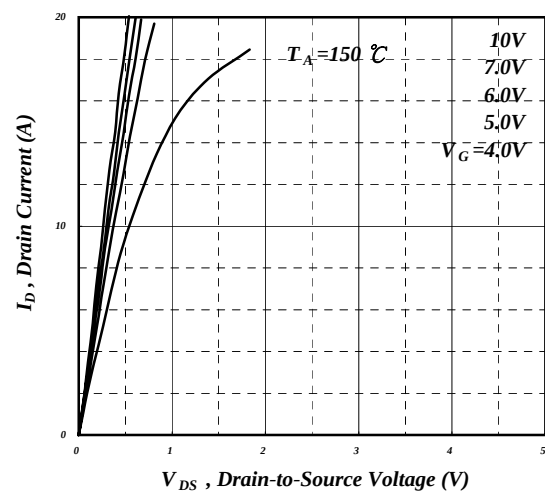


Fig 2. Typical Output Characteristics

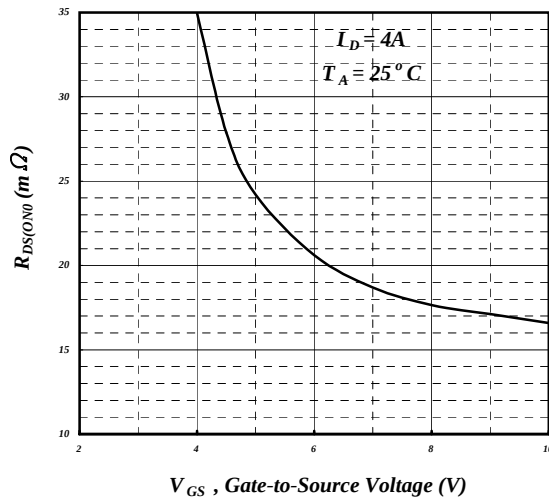
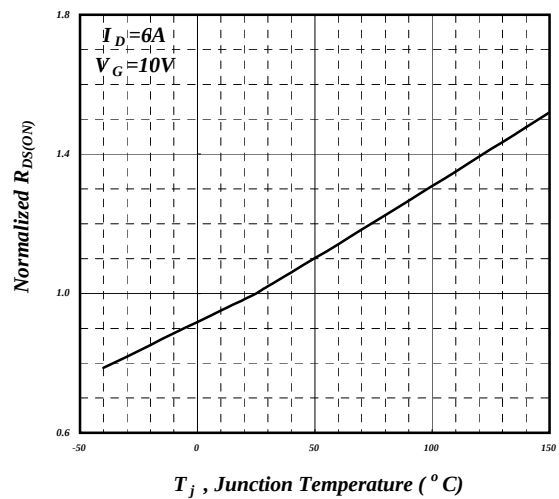
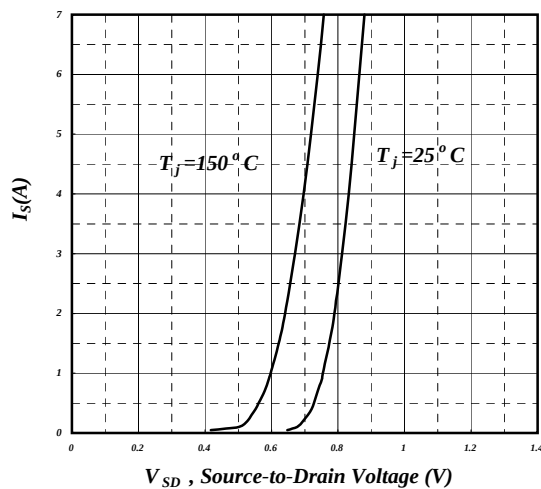
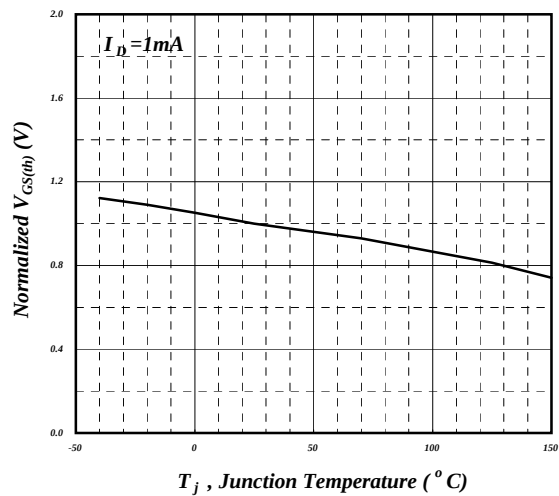


Fig 3. On-Resistance v.s. Gate Voltage

Fig 4. Normalized On-Resistance
v.s. Junction TemperatureFig 5. Forward Characteristic of
Reverse DiodeFig 6. Gate Threshold Voltage v.s.
Junction Temperature

N-Channel

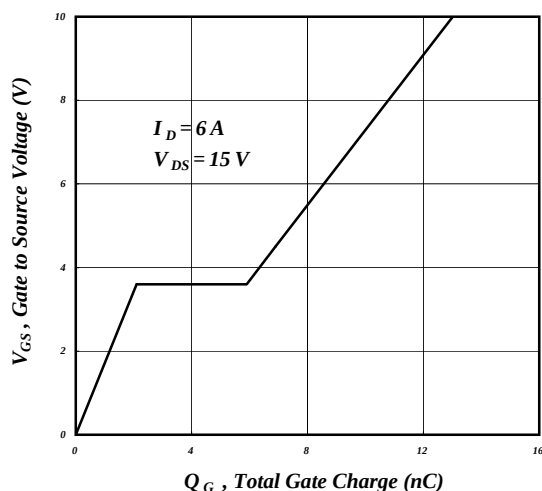


Fig 7. Gate Charge Characteristics

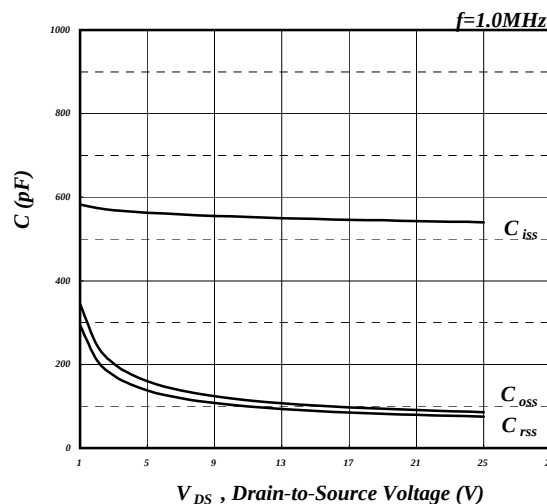


Fig 8. Typical Capacitance Characteristics

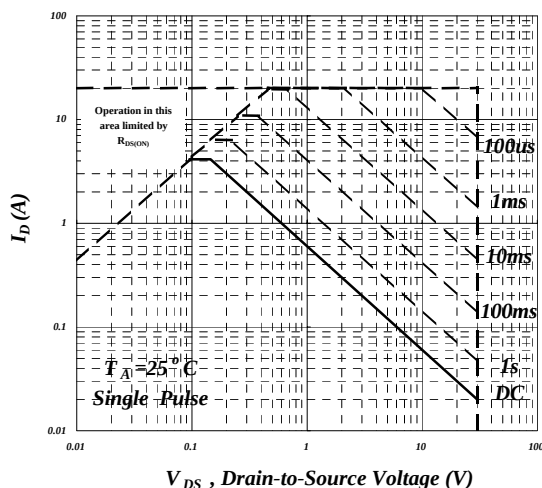


Fig 9. Maximum Safe Operating Area

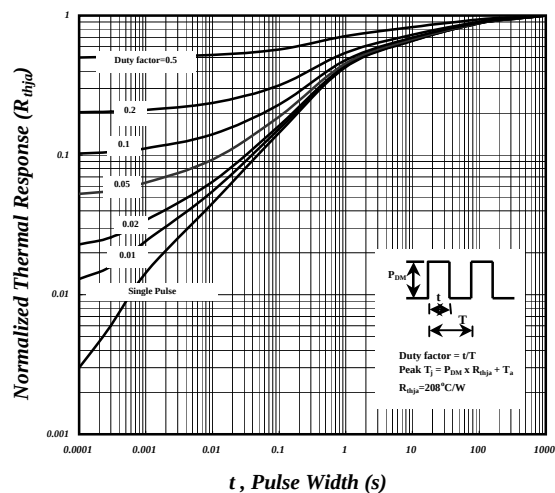


Fig 10. Effective Transient Thermal Impedance

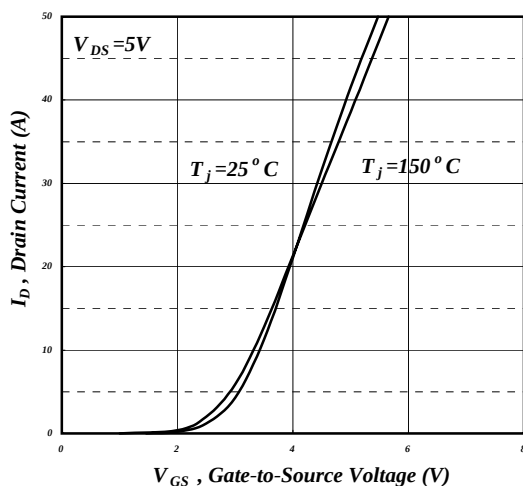


Fig 11. Transfer Characteristics

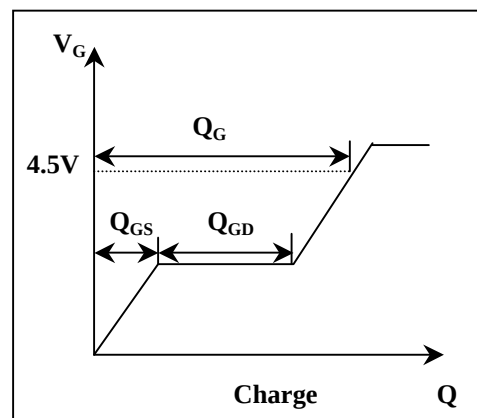


Fig 12. Gate Charge Waveform

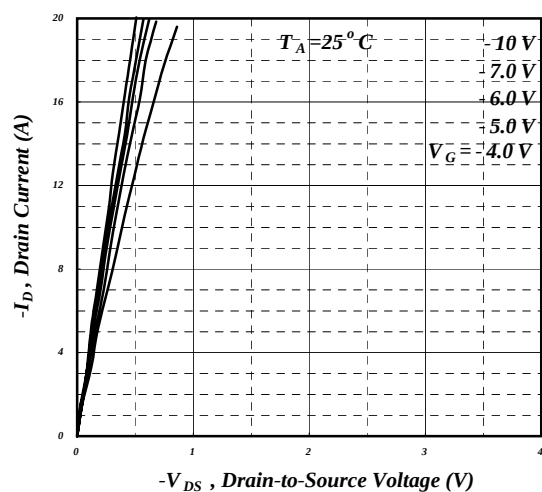


Fig 1. Typical Output Characteristics

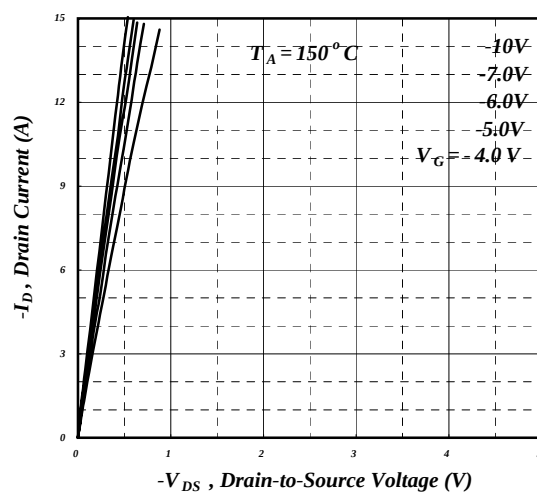


Fig 2. Typical Output Characteristics

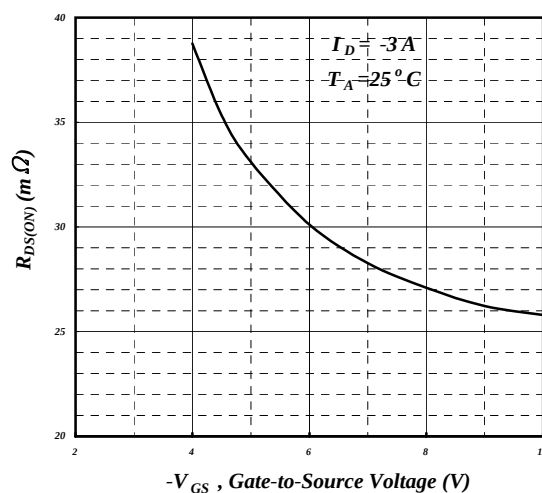
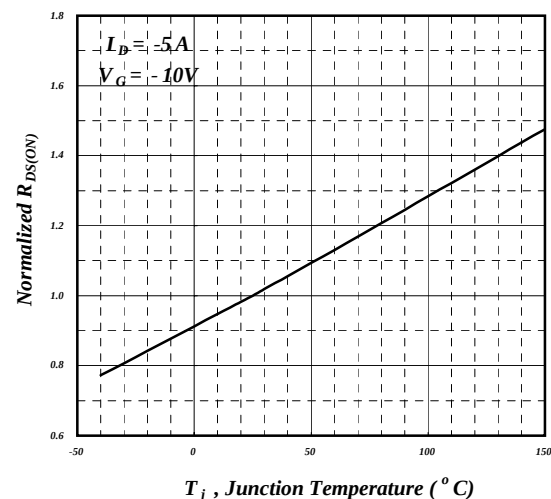
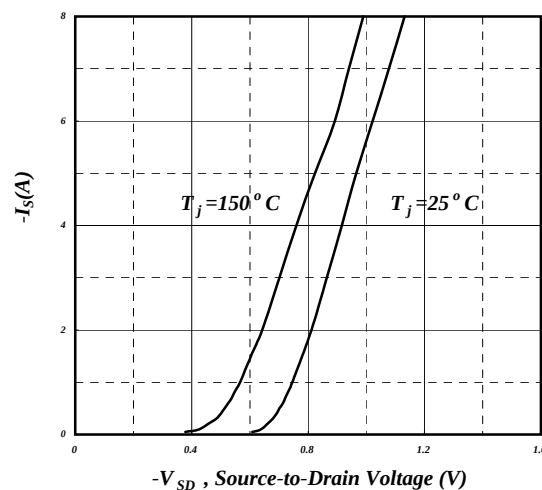
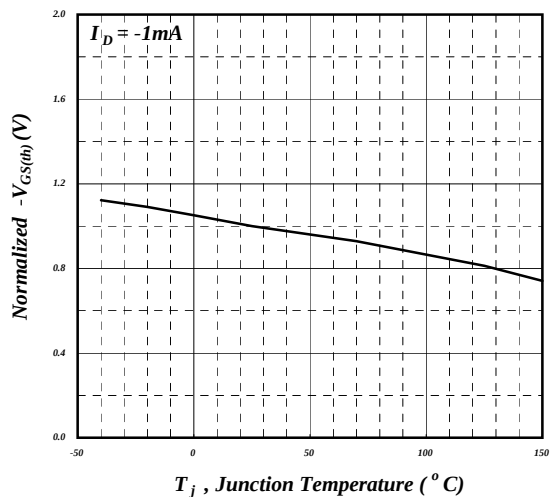


Fig 3. On-Resistance v.s. Gate Voltage

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Junction Temperature

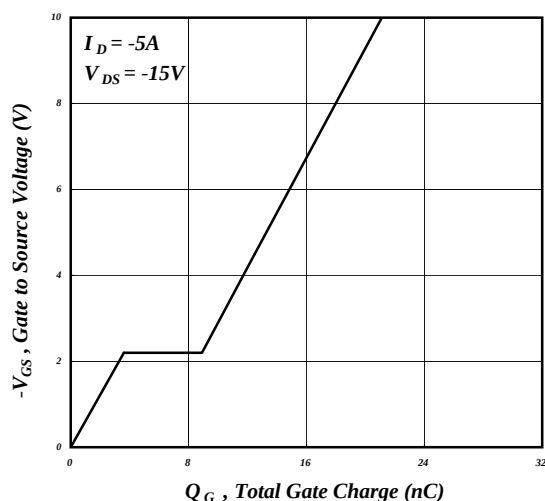


Fig 7. Gate Charge Characteristics

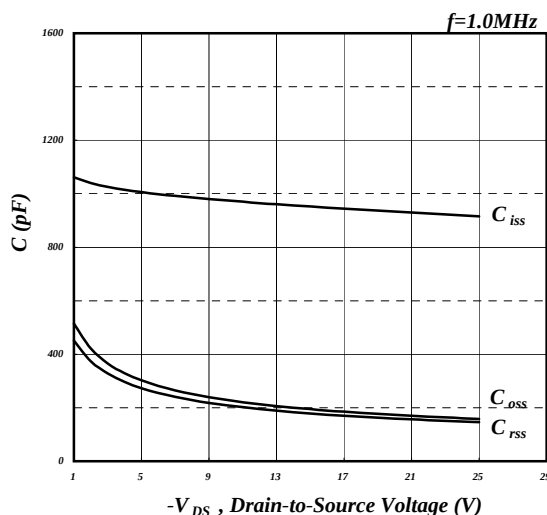


Fig 8. Typical Capacitance Characteristics

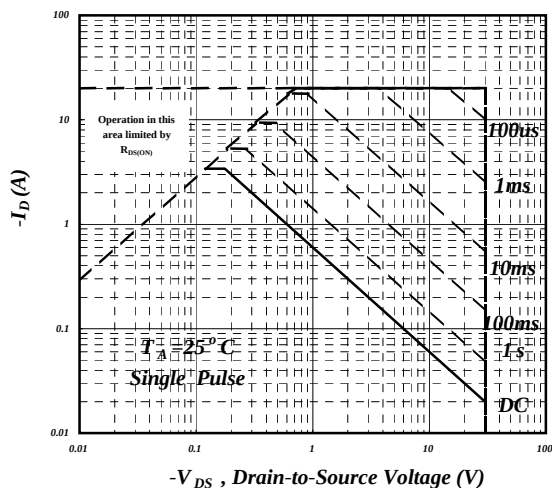


Fig 9. Maximum Safe Operating Area

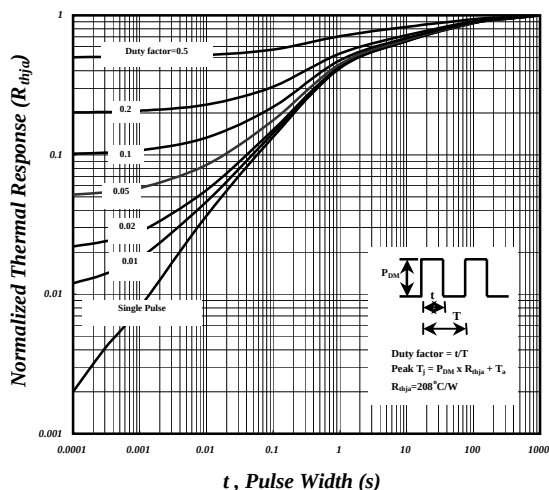


Fig 10. Effective Transient Thermal Impedance

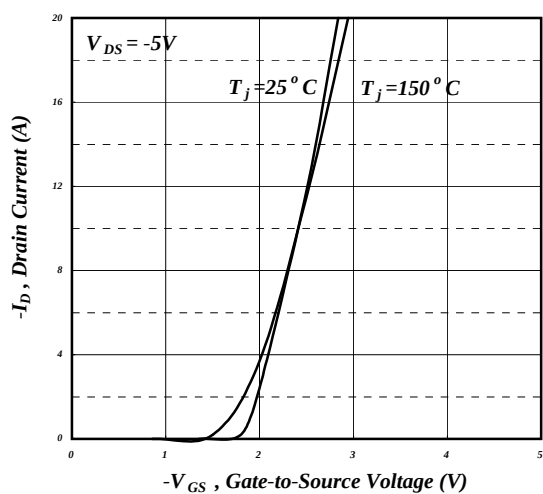


Fig 11. Transfer Characteristics

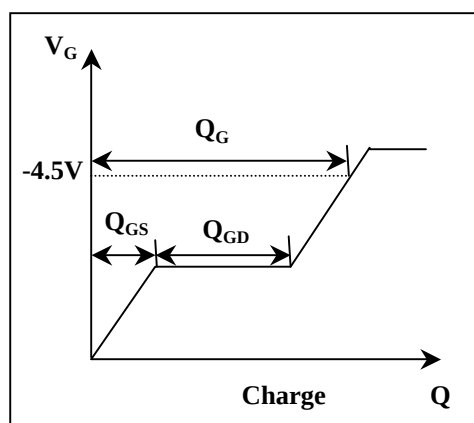
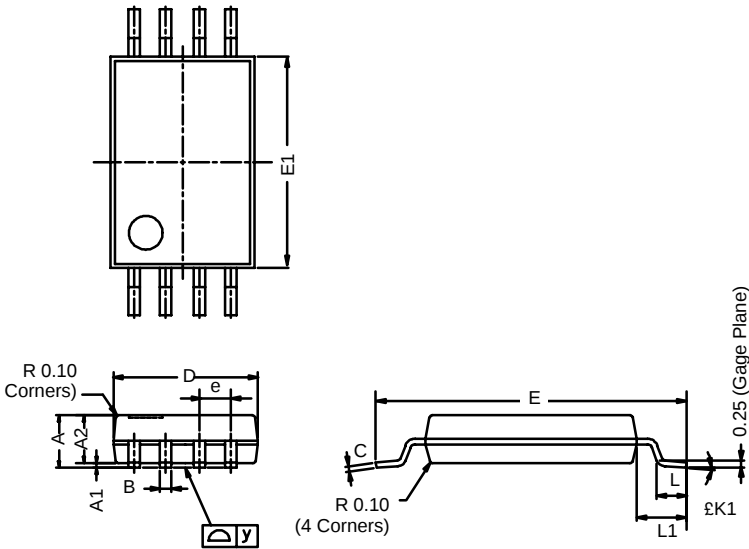


Fig 12. Gate Charge Waveform

TSSOP: 8-LEAD
JEDEC Part Number: MO-153



Dim	MILLIMETERS		
	Min	Nom	Max
A	—	—	1.20
A ₁	0.05	0.10	0.15
A ₂	0.80	1.00	1.05
B	0.19	0.28	0.30
C	—	0.127	—
D	2.90	3.00	3.10
E	6.20	6.40	6.60
E ₁	4.30	4.40	4.50
e	—	0.65	—
L	0.45	0.60	0.75
L ₁	0.90	1.00	1.10
Y	—	—	0.10
UK1	0°	3°	6°
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5844			

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